

	No.1030E	2SB926/2SD1246 PNP/NPN Epitaxial Planar Silicon Transistors Large-Current Driving Applications

Applications

- Power supplies, relay drivers, lamp drivers, electrical equipment

Features

- Adoption of FBET, MBIT processes
- Low saturation voltage
- Large current capacity and wide ASO

(): 2SB926

Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$

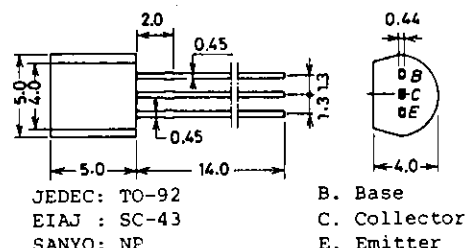
			unit
Collector to base voltage	V_{CB0}	(-)30	V
Collector to emitter voltage	V_{CEO}	(-)25	V
Emitter to base voltage	V_{EBO}	(-)6	V
Collector current	I_C	(-)2	A
Collector Current(Pulse)	I_{CP}	(-)5	A
Collector dissipation	P_C	0.75	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

Electrical Characteristics/ $T_a = 25^\circ\text{C}$

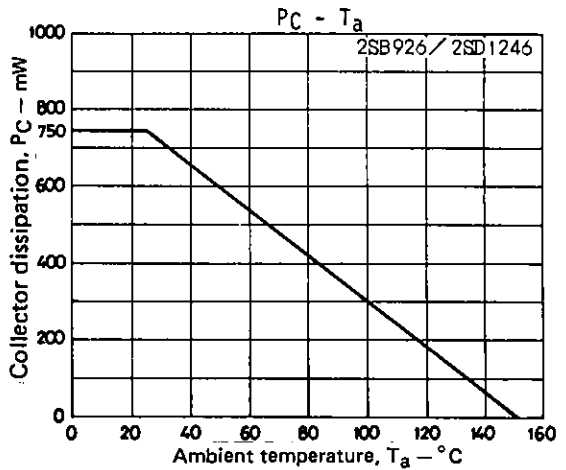
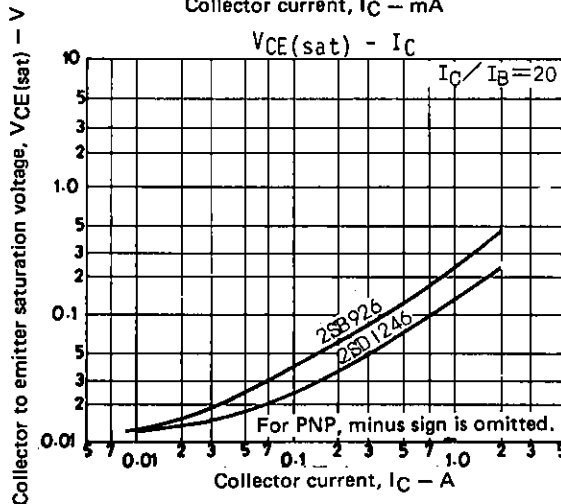
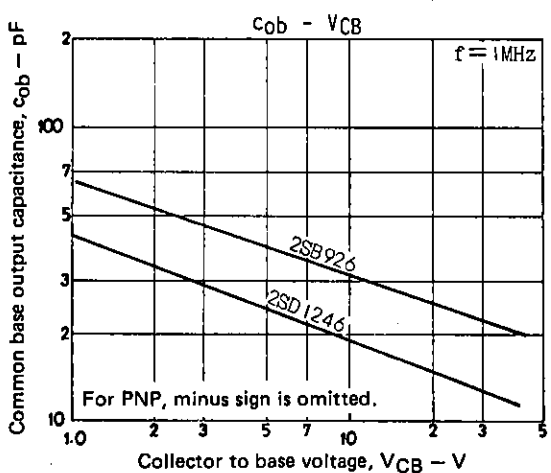
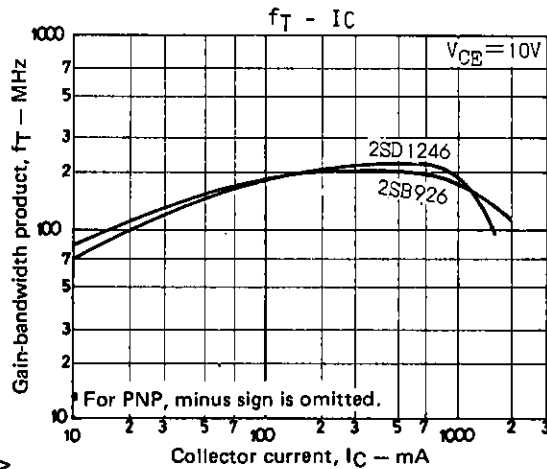
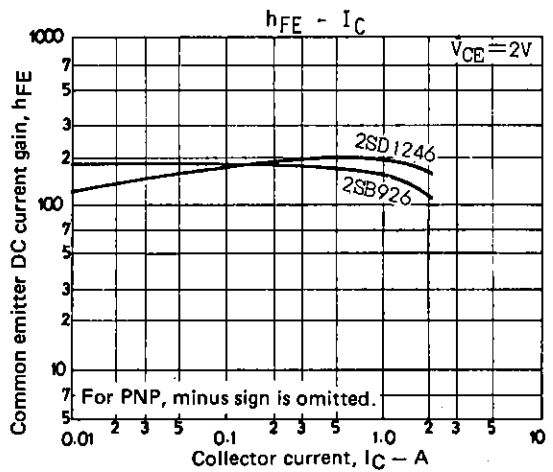
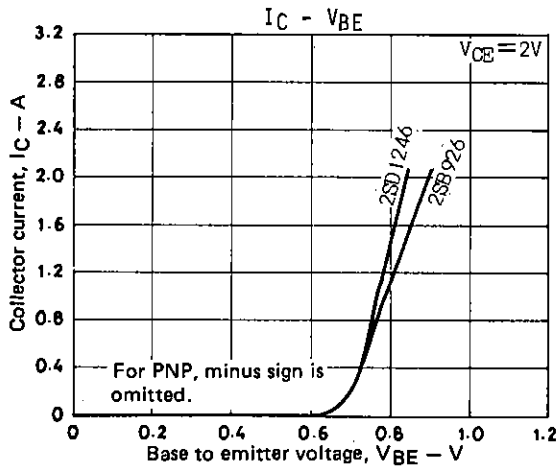
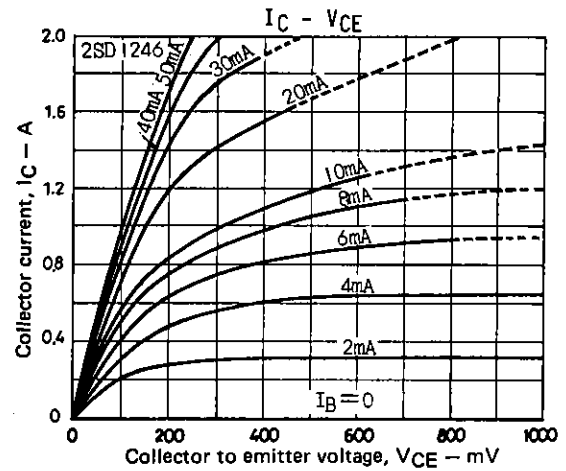
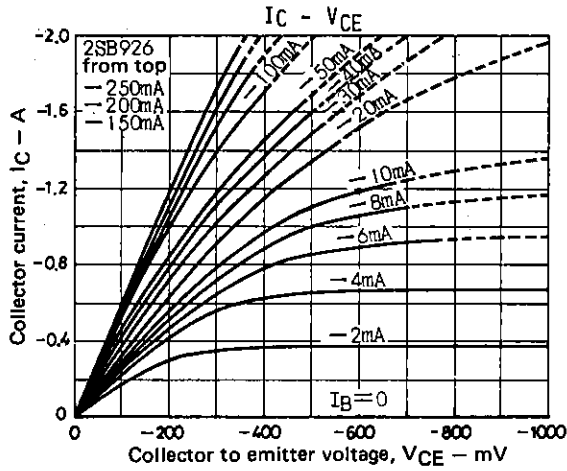
			min	typ	max	unit
Collector cutoff current	I_{CBO}	$V_{CB} = (-)20\text{ V}, I_E = 0$			(-)0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = (-)4\text{ V}, I_C = 0$			(-)0.1	μA
DC current gain	$h_{FE}(1)$	$V_{CE} = (-)2\text{ V}, I_C = (-)100\text{ mA}$	100*		560*	
	$h_{FE}(2)$	$V_{CE} = (-)2\text{ V}, I_C = (-)1.5\text{ A, pulse}$	65	130		
Gain-bandwidth product	f_T	$V_{CE} = (-)10\text{ V}, I_C = (-)50\text{ mA}$		150		MHz
Common base output capacitance	c_{ob}	$V_{CB} = (-)10\text{ V}, f = 1\text{ MHz}$		19		pF
				(32)		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = (-)1.5\text{ A}, I_B = (-)75\text{ mA, pulse}$		0.18	0.4	V
				(-0.35)	(-0.6)	
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = (-)1.5\text{ A}, I_B = (-)75\text{ mA}$		(-)0.85	(-)1.2	V
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = (-)10\text{ }\mu\text{A}, I_E = 0$	(-)30			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{ mA}, R_{BE} = \infty$	(-)25			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = (-)10\text{ }\mu\text{A}, I_C = 0$	(-)6			V

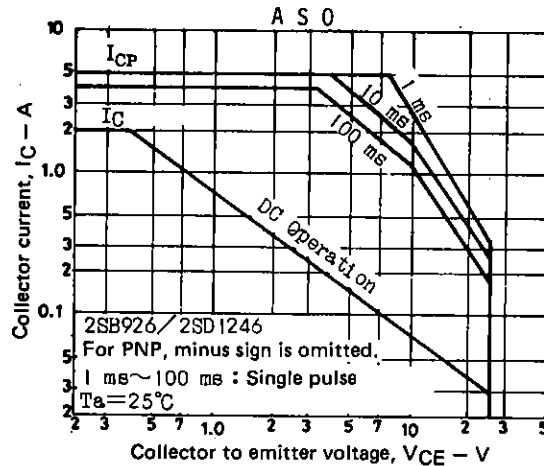
* The 2SB926/2SD1246 are classified by 100 mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400	280	U	560
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Package Dimensions 2003A
 (unit: mm)


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